



**JST16Q**

**TRITC**

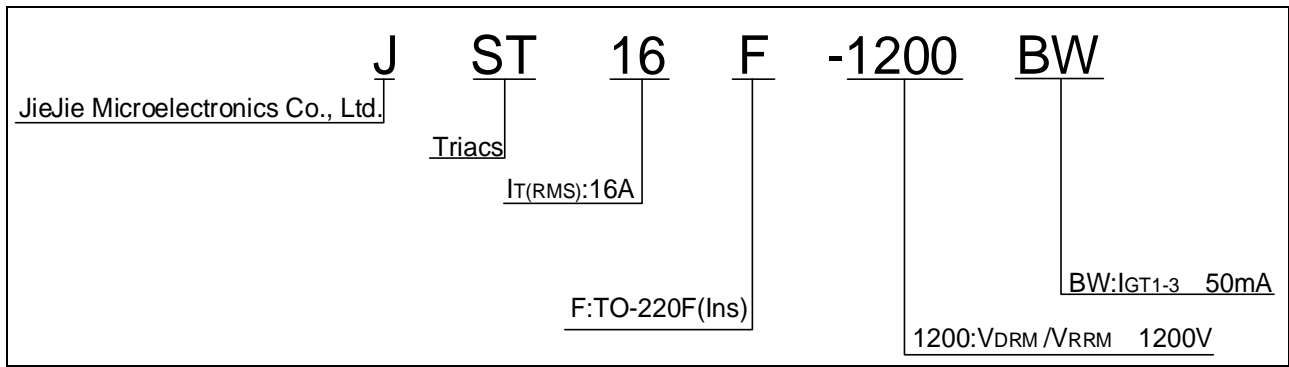


Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	4	kV

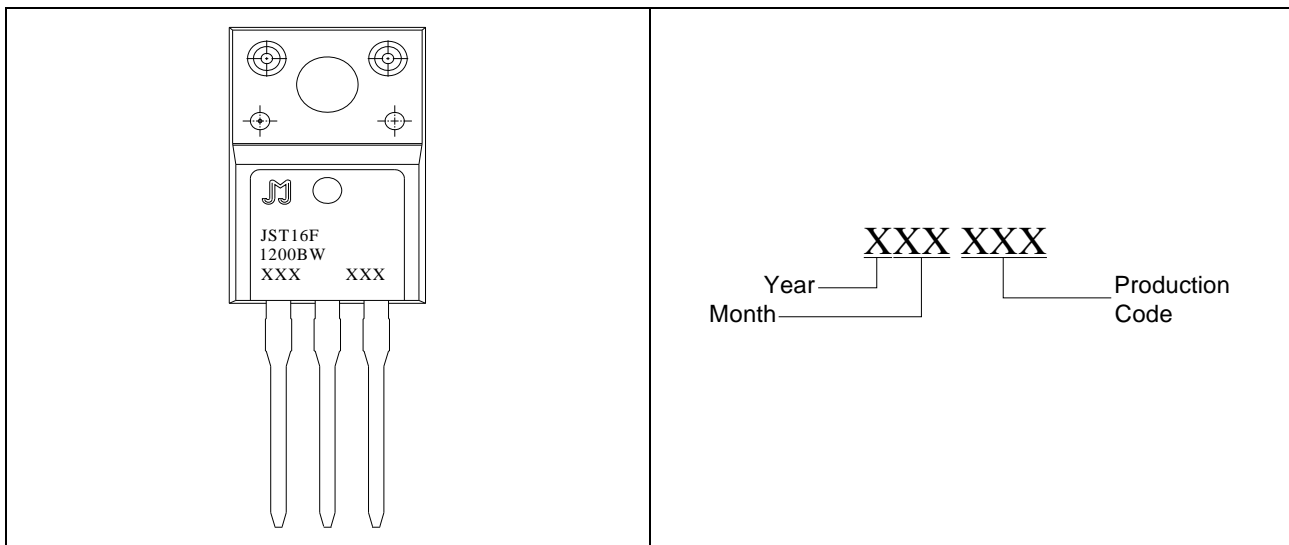
**ELECTRICAL CHARACTERISTICS** ( $T_j=25$  unless otherwise specified)

<b>Symbol</b>	<b>Test Condition</b>	<b>Quadrant</b>	<b>Value</b>	<b>-</b>	<b>-Unit</b>
$I_{GT}$	$V_D=12V$ $R_L=33$	- -	MAX.	50	mA

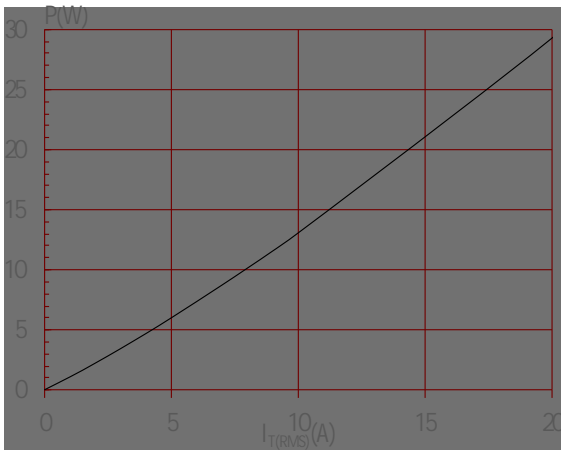
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MARKING



**FIG.1:** Maximum power dissipation versus RMS on-state current



**FIG.2:** RMS on-state current versus case temperature

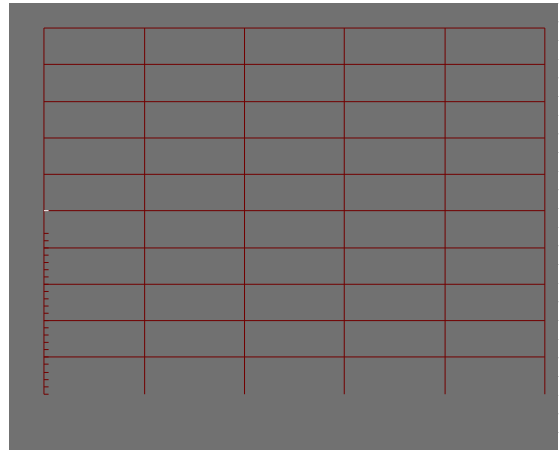


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards







PACKAGE MECHANICAL DATA

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